

ABSTRACT

Provided is a method for cleaning a mask for vacuum vapor deposition, the method comprising cleaning a mask with a cleaning composition containing at least one member selected from N-methyl-2-pyrrolidinone and N,N-dimethylformamide, and
5 rinsing the mask after cleaning, with a rinsing composition containing at least one hydrofluoroether selected from HFE-347pc-f, HFE-254pc, HFE-356pcf and HFE-449mec-f. According to this cleaning method, at the time of rinsing off the cleaning composition in the cleaning of a mask that has been used in a vacuum vapor deposition process in the production of an organic EL device, it is possible to clean the mask so as
10 to be extremely clean without resulting in decomposition of an active ingredient.